

## MDMA700P1800CC

tentative

## **Standard Rectifier Module**

= 2x 1800 V

700 A

 $V_{\mathsf{F}}$ 1.05 V

## Phase leg

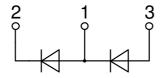
#### Part number

#### MDMA700P1800CC



Backside: isolated

**F1** E72873



#### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

#### **Applications:**

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

#### Package: ComPack

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

#### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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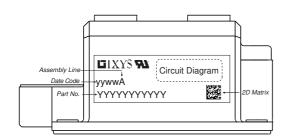
Rectifier				1	Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V <sub>RSM</sub>	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			1900	V	
V <sub>RRM</sub>	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1800	V	
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1800 V	$T_{VJ} = 25^{\circ}C$			500	μΑ	
		$V_R = 1800 \text{ V}$	$T_{VJ} = 150$ °C			20	mA	
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 700 A	$T_{VJ} = 25^{\circ}C$			1.14	V	
		$I_F = 1400 \text{ A}$				1.35	٧	
		$I_F = 700 \text{ A}$	$T_{VJ} = 125$ °C			1.05	٧	
		$I_F = 1400 \text{ A}$				1.30	V	
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 100°C	$T_{VJ} = 150$ °C			700	Α	
		rectangular $d = 0.5$						
V <sub>F0</sub>	threshold voltage	de en entre de Maria en entre	$T_{VJ} = 150$ °C			0.78	٧	
r <sub>F</sub>	slope resistance	loss calculation only				0.35	mΩ	
R <sub>thJC</sub>	thermal resistance junction to ca	ase				0.055	K/W	
R <sub>thCH</sub>	thermal resistance case to heats	sink			0.02		K/W	
P <sub>tot</sub>	total power dissipation		T <sub>C</sub> = 25°C			2270	W	
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			20.0	kA	
		t = 8,3  ms; (60 Hz), sine	$V_R = 0 V$			21.6	kA	
		t = 10 ms; (50 Hz), sine	T <sub>VJ</sub> = 150°C			17.0	kA	
		t = 8,3  ms; (60 Hz), sine	$V_R = 0 V$			18.4	kA	
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			2.00	MA <sup>2</sup> s	
		t = 8,3  ms; (60 Hz), sine	$V_R = 0 V$			1.94	MA <sup>2</sup> s	
		t = 10 ms; (50 Hz), sine	T <sub>VJ</sub> = 150°C			1.45	MA <sup>2</sup> s	
		t = 8.3  ms; (60 Hz), sine	$V_R = 0 V$			1.40	MA <sup>2</sup> s	
CJ	junction capacitance	$V_{R} = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		781		рF	



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Package ComPack			Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal				1200	Α
T <sub>vJ</sub>	virtual junction temperature			-40		150	°C
Top	operation temperature			-40		125	°C
T <sub>stg</sub>	storage temperature			-40		125	°C
Weight					500		g
M <sub>D</sub>	mounting torque			3		5	Nm
$\mathbf{M}_{_{T}}$	terminal torque			12		14	Nm
d <sub>Spp/App</sub>	eroonago dietaneo on curtaco l	striking distance through air	terminal to terminal	21.0			mm
$d_{Spb/Apb}$	creepage distance on surface	age distance on surface   striking distance through air terminal to backside		18.0			mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second		4800			٧
.002	$t = 1 \text{ minute}$ 50/60 Hz, RMS; IsoL $\leq 1$		50/60 Hz, RMS; lisoL ≤ 1 mA	4000			٧



### Part description

M = Module

D = Diode
M = Standard Rectifier

A = (up to 1800V) 700 = Current Rating [A]

P = Phase leg

1800 = Reverse Voltage [V]

CC = ComPack

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA700P1800CC	MDMA700P1800CC	Box	3	

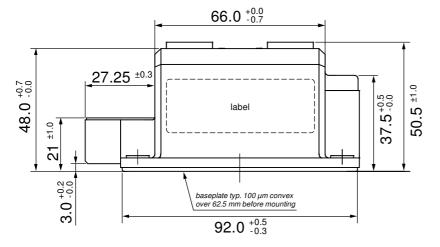
<b>Equivalent Circuits for Simulation</b>			* on die level	T <sub>vJ</sub> = 150 °C
$I \rightarrow V_0$	$-R_0$	Rectifier		
V <sub>0 max</sub>	threshold voltage	0.78		V
$R_{0\;max}$	slope resistance *	0.16		$m\Omega$

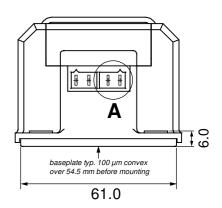


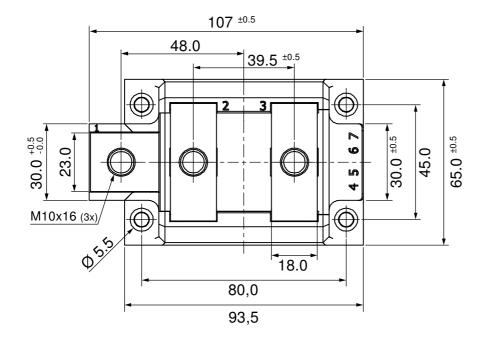
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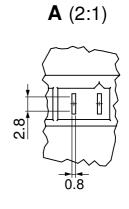
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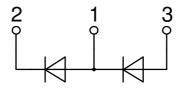
### **Outlines ComPack**











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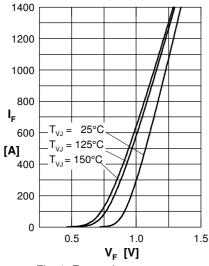


Fig. 1 Forward current versus voltage drop per diode

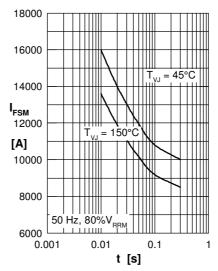


Fig. 2 Surge overload current vs. time per diode

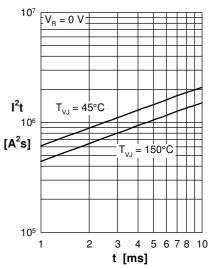


Fig. 3 I2t versus time per diode

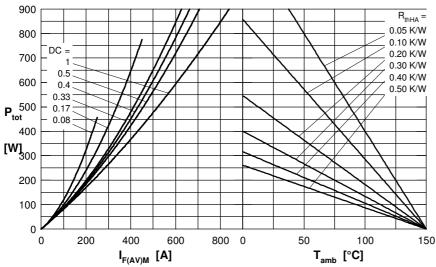


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

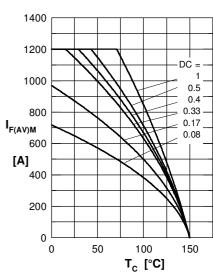


Fig. 5 Max. forward current vs. case temperature per diode

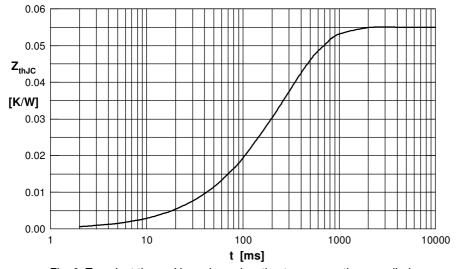


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for  $Z_{\text{thJC}}$  calculation:

i	$R_{thi}$ (K/W)	t <sub>i</sub> (s)
1	0.001	0.0150
2	0.004	0.0600
3	0.017	0.2000
4	0.033	0.3400